

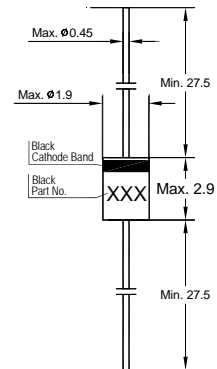
RB441Q-40

SILICON EPITAXIAL PLANAR TYPE SCHOTTKY BARRIER DIODES

for low current rectification

Features

- Low forward rise voltage (V_F)
- Small pitch enables insertion on PCBs
- Glass sealed envelope for high reliability



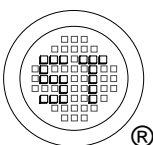
Glass Case DO-34
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	100	mA
Peak Forward Surge Current	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	- -	0.34 0.55	V
Reverse Current at $V_R = 40\text{ V}$	I_R	-	100	μA
Terminal Capacitance at $V_R = 10\text{ V}$, $f = 1\text{ MHz}$	C_T	6	-	pF



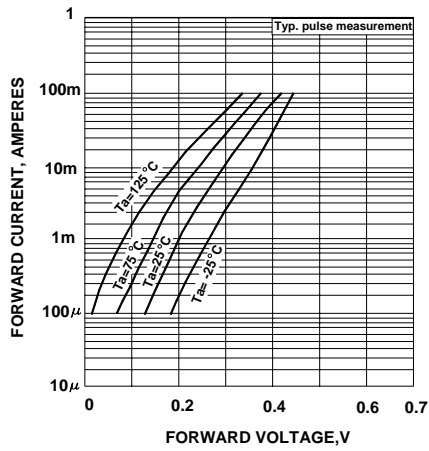
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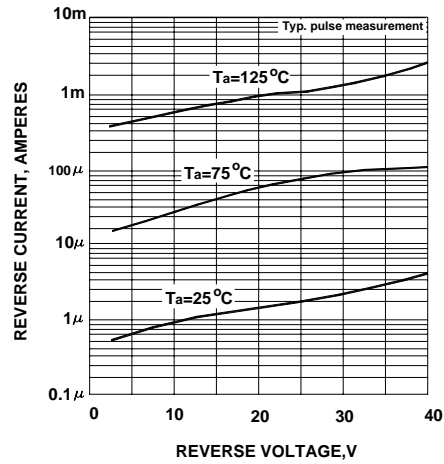
Dated : 25/06/2007

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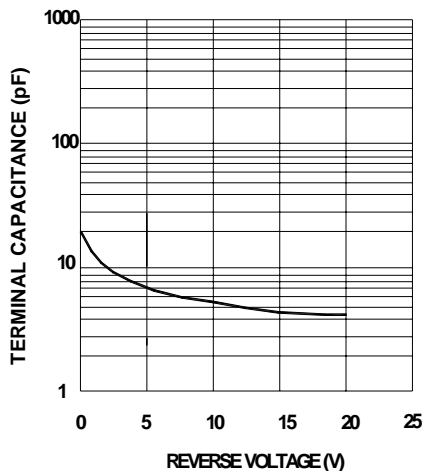
FORWARD CHARACTERISTICS



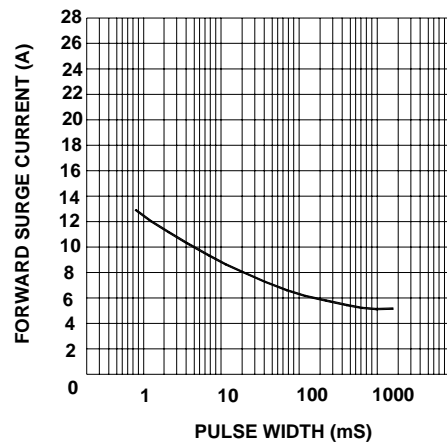
REVERSE CHARACTERISTICS



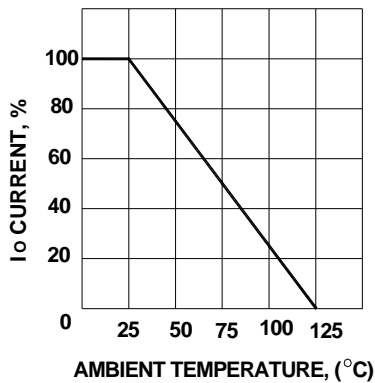
TERMINAL CAPACITANCE CHARACTERISTICS



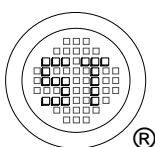
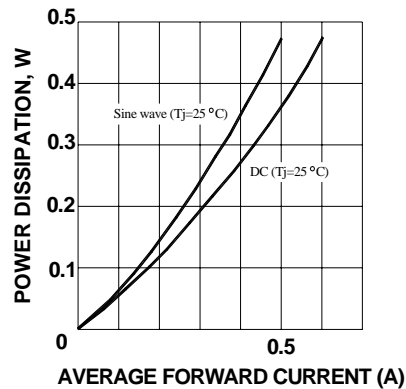
FORWARD SURGE CURRENT CHARACTERISTIC



DERATING CURVE
(mounting on glass epoxy PCBs)



MEAN RECTIFYING CURRENT CHARACTERISTICS



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